

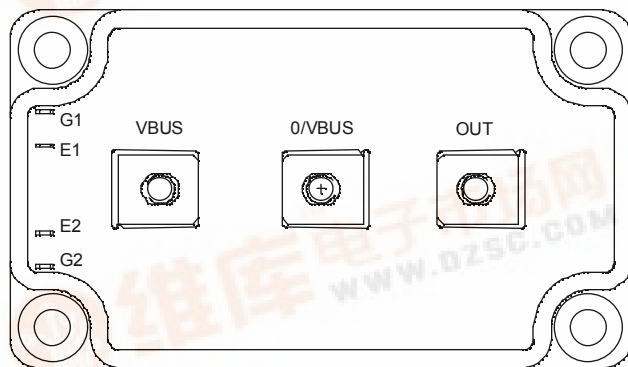
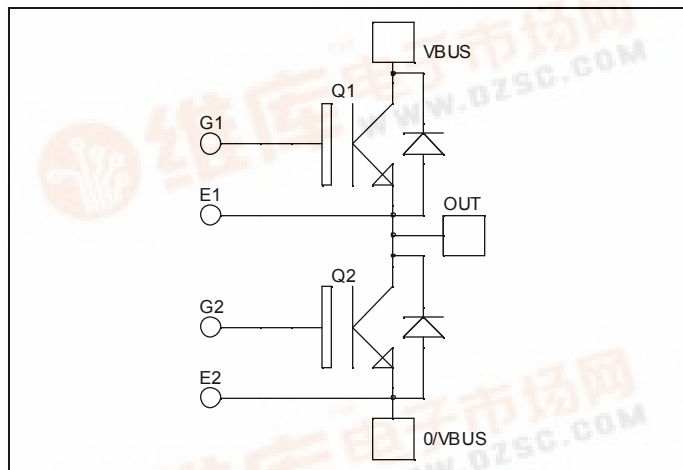


APTGT225A170G

Phase leg Trench + Field Stop IGBT[®] Power Module

$$V_{CES} = 1700V$$

$$I_C = 225A @ T_c = 80^{\circ}C$$



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT[®] Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_C = 25^{\circ}C$ 340 $T_C = 80^{\circ}C$ 225	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$ 450	
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^{\circ}C$ 1250	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$ 450A @ 1600V	

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$			500	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 225A$	$T_j = 25^\circ\text{C}$	2.0	2.4	V
			$T_j = 125^\circ\text{C}$	2.4		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4mA$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		20		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.8		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		0.66		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 900V$ $I_C = 225A$ $R_G = 3.3\Omega$		370		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 900V$ $I_C = 225A$ $R_G = 3.3\Omega$		400		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			800		
T_f	Fall Time			300		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 900V$ $I_C = 225A$ $R_G = 3.3\Omega$	$T_j = 125^\circ\text{C}$	72		mJ
E_{off}	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$	70.5		

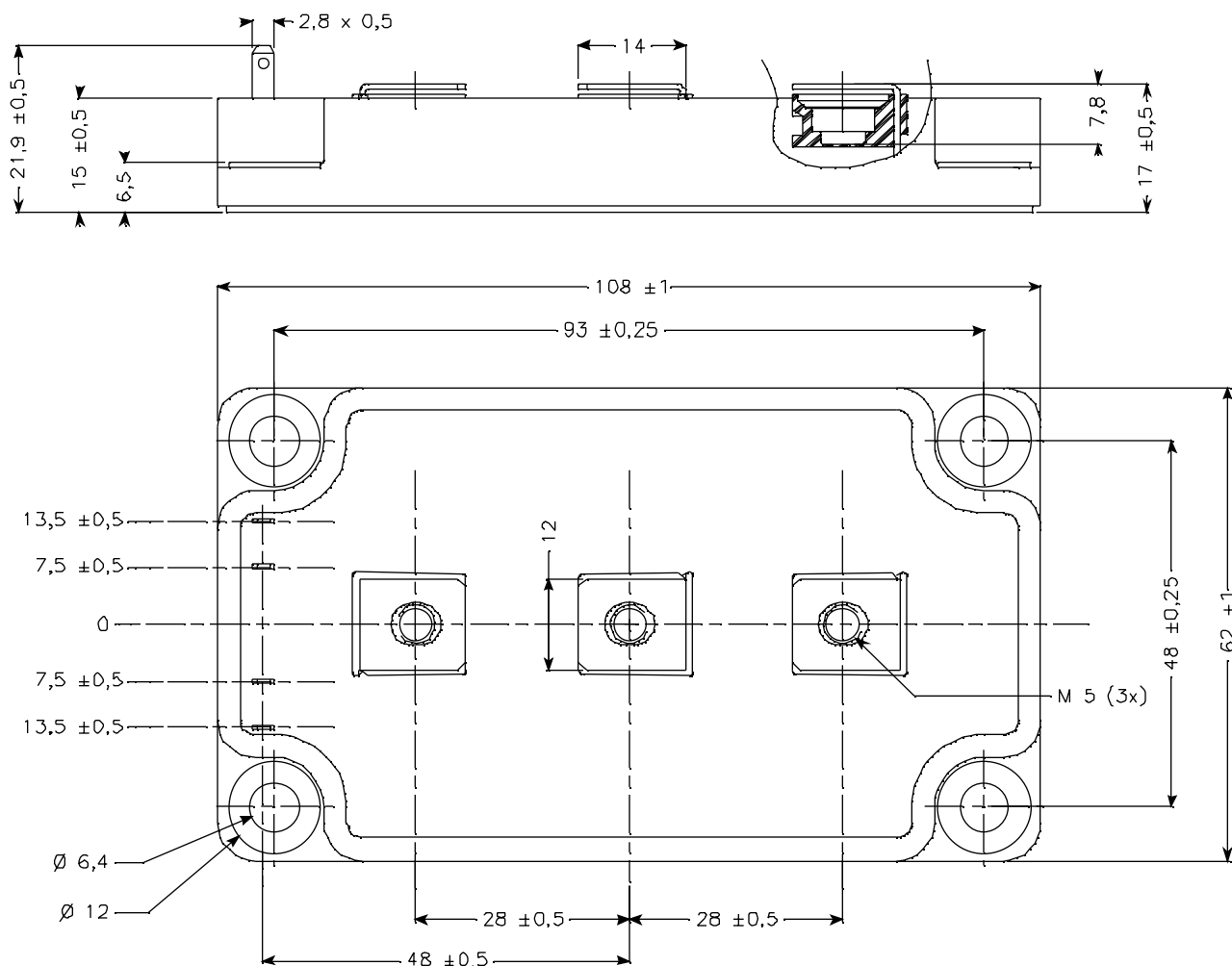
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1700V$	$T_j = 25^\circ\text{C}$		500	μA
			$T_j = 125^\circ\text{C}$		750	
I_F	DC Forward Current		$T_c = 80^\circ\text{C}$	225		A
V_F	Diode Forward Voltage	$I_F = 225A$	$T_j = 25^\circ\text{C}$	1.8	2.2	V
			$T_j = 125^\circ\text{C}$	1.9		
t_{rr}	Reverse Recovery Time	$I_F = 225A$ $V_R = 900V$ $di/dt = 2400A/\mu s$	$T_j = 25^\circ\text{C}$	385		ns
			$T_j = 125^\circ\text{C}$	490		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	57		μC
			$T_j = 125^\circ\text{C}$	93		
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	26		mJ
			$T_j = 125^\circ\text{C}$	52		

Thermal and package characteristics

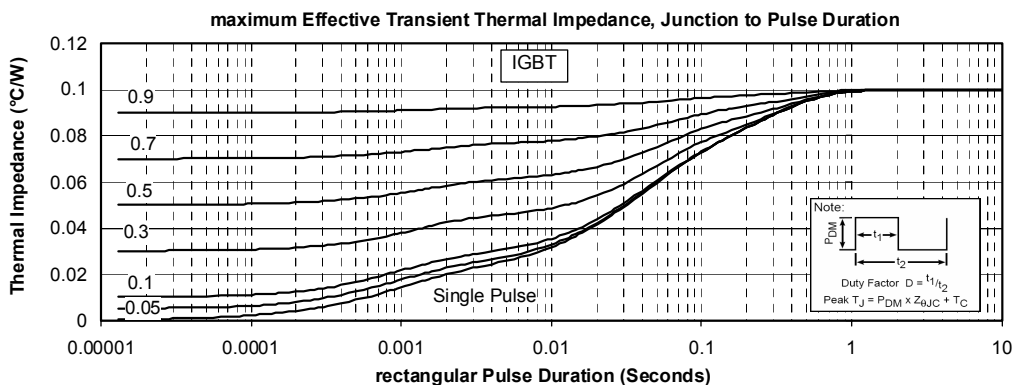
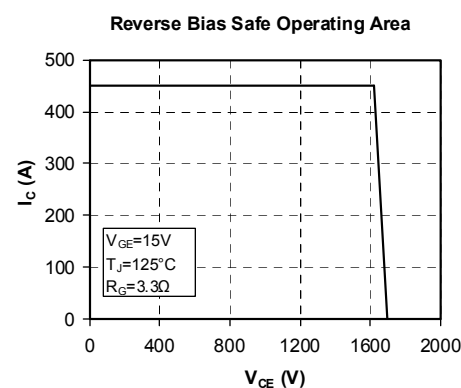
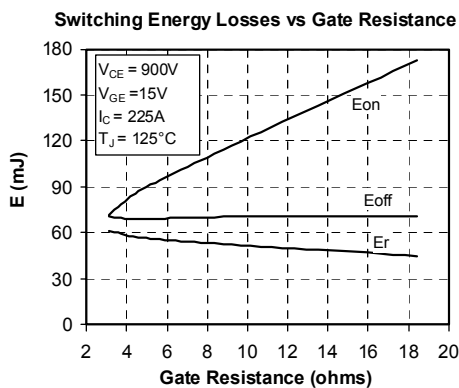
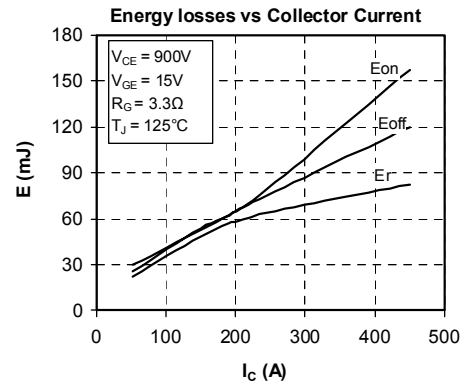
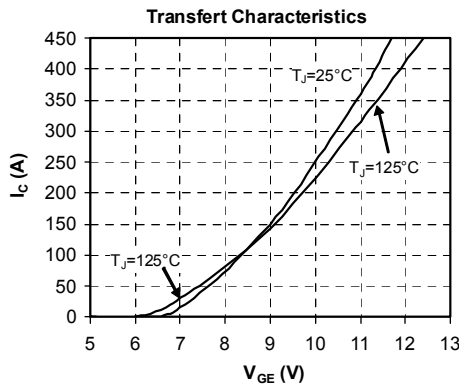
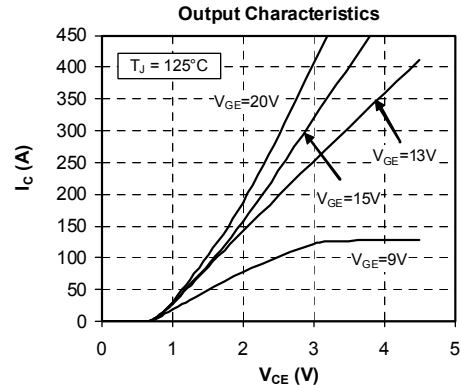
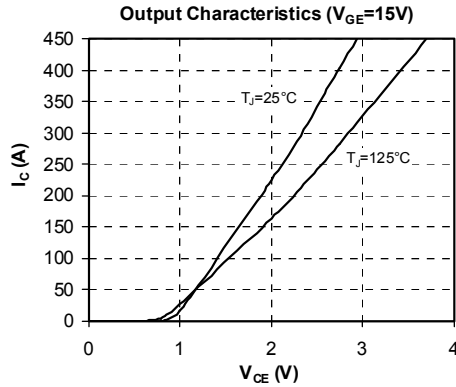
Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.1	°C/W
		Diode			0.18	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		3500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				280	g

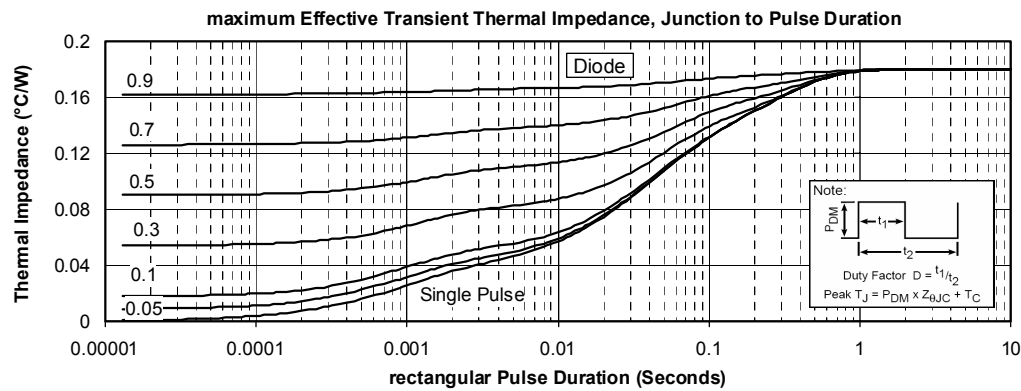
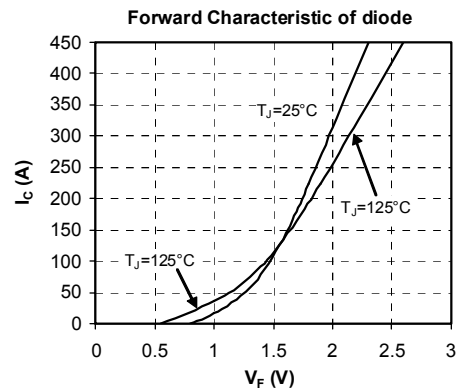
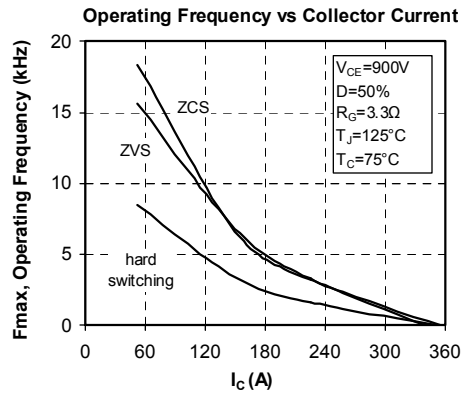
SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve





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